NSN 5962-00-506-6864

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View Online at https://aerobasegroup.com/nsn/5962-00-506-6864

Between 0.745 inches and 0.785 inches

Body Width:

Between 0.240 inches and 0.260 inches

Body Height:

Between 0.095 inches and 0.140 inches

Maximum Power Dissipation Rating:

400.0 milliwatts

Operating Tempurature Range:

+0.0/+75.0 degrees celsius

Storage Tempurature Range:

-65.0/+175.0 degrees celsius

Features Provided:

Bipolar and monolithic and positive outputs and programmable and programmed and w/enable and w/buffered output and w/open collector and w/decoded output and high speed

Inclosure Material:

Plastic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

6 input

Case Outline Source And Designator:

-0-001-ae joint electron device engineering council

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

50.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

33048-41-010085 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

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